

General Description

SFGMOS[®]

$R_{DS(ON)}$, low gate charge, fast switching and excellent avalanche characteristics. The high V_{th} series is specially optimized for high systems with gate driving voltage greater than 10V.

Features

- Low $R_{DS(ON)}$ & FOM
- Extremely low switching loss
- Excellent stability and uniformity
- Fast switching and soft recovery



Applications

- Switched mode power supply
- Motor driver
- Battery protection
- DC-DC convertor
- Solar inverter
- UPS and energy inverter

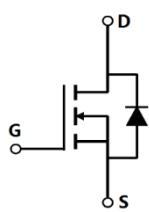
Key Performance Parameters

Parameter	Value	Unit
$V_{DS, min} @ T_{j(max)}$	100	V
$I_D, pulse$	300	A
$R_{DS(ON), max} @ V_{GS}=10V$	8	
Q_g	55.6	nC

Marking Information

Product Name	Package	Marking
SFG100N10KF	TO263	SFG100N10K

Package & Pin information



Absolute Maximum Ratings at $T_j=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain source voltage	V_{DS}	100	V
Gate source voltage	V_{GS}	± 20	V
Continuous drain current ¹⁾ , $T_C=25^\circ\text{C}$	I_D	100	A
Pulsed drain current ²⁾ , $T_C=25^\circ\text{C}$	$I_{D,\text{pulse}}$	300	A
Continuous diode forward current ¹⁾ , $T_C=25^\circ\text{C}$	I_S	100	A
Diode pulsed current ²⁾ , $T_C=25^\circ\text{C}$	$I_{S,\text{pulse}}$	300	A
Power dissipation ³⁾ , $T_C=25^\circ\text{C}$	P_D	148	W
Single pulsed avalanche energy ⁵⁾	E_{AS}	130	mJ
Operation and storage temperature	T_{stg}, T_j	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	R	0.84	$^\circ\text{C}/\text{W}$
Thermal resistance, junction-ambient ⁴⁾	R	62	$^\circ\text{C}/\text{W}$

Electrical Characteristics at $T_j=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	100			V	$V_{GS}=0 \text{ V}, I_D=250 \text{ A}$
Gate threshold voltage	$V_{GS(\text{th})}$	2.0		4.0	V	$V_{DS}=V_{GS}, I_D=250 \text{ A}$
Drain-source on-state resistance	$R_{DS(\text{ON})}$		6.5	8.0		$V_{GS}=10 \text{ V}, I_D=12 \text{ A}$
Gate-source leakage current	I_{GSS}			100	nA	$V_{GS}=20 \text{ V}$
				-100		$V_{GS}=-20 \text{ V}$
Drain-source leakage current	I_{DSS}			1	A	$V_{DS}=100 \text{ V}, V_{GS}=0 \text{ V}$

SFG100N10KF

Enhancement Mode N-

Electrical Characteristics Diagrams

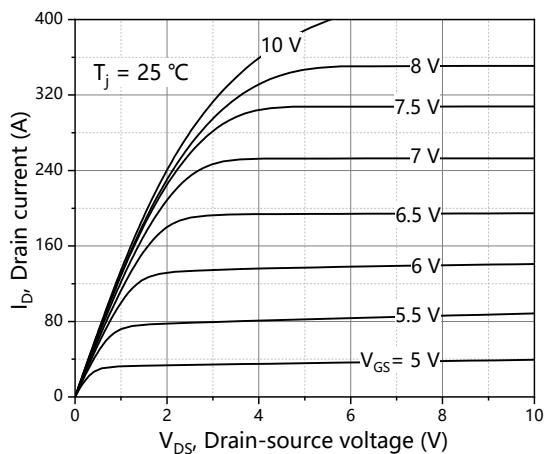


Figure 1. Typ. output characteristics

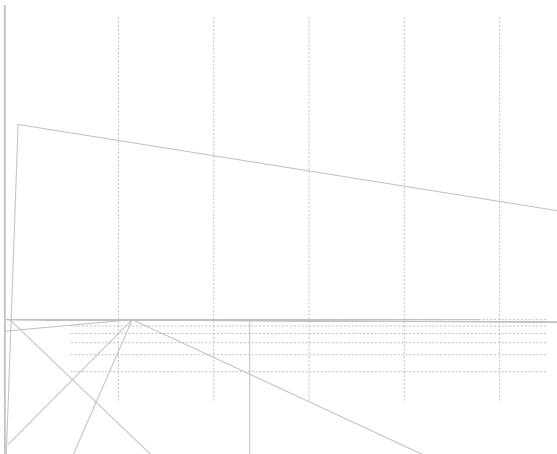


Figure 2. Typ. transfer characteristics

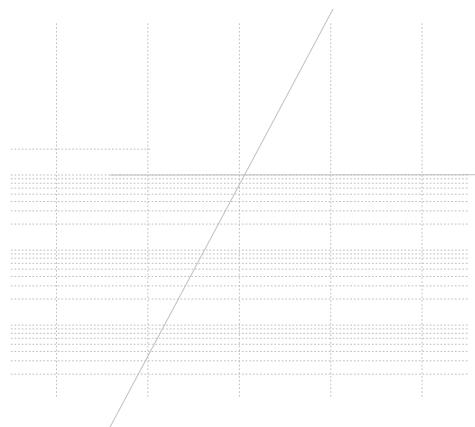


Figure 3. Typ. capacitances



Figure 4. Typ. gate charge

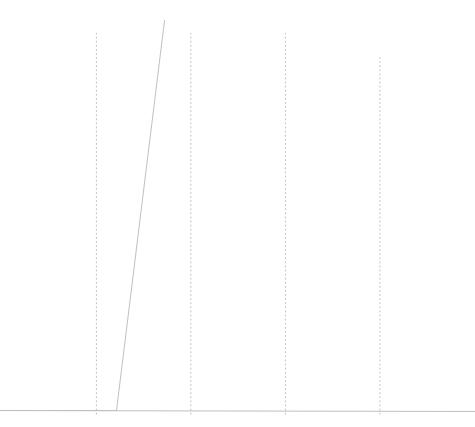


Figure 5. Drain-source breakdown voltage

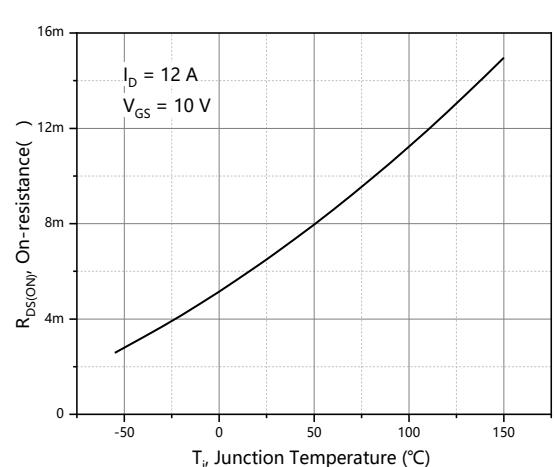
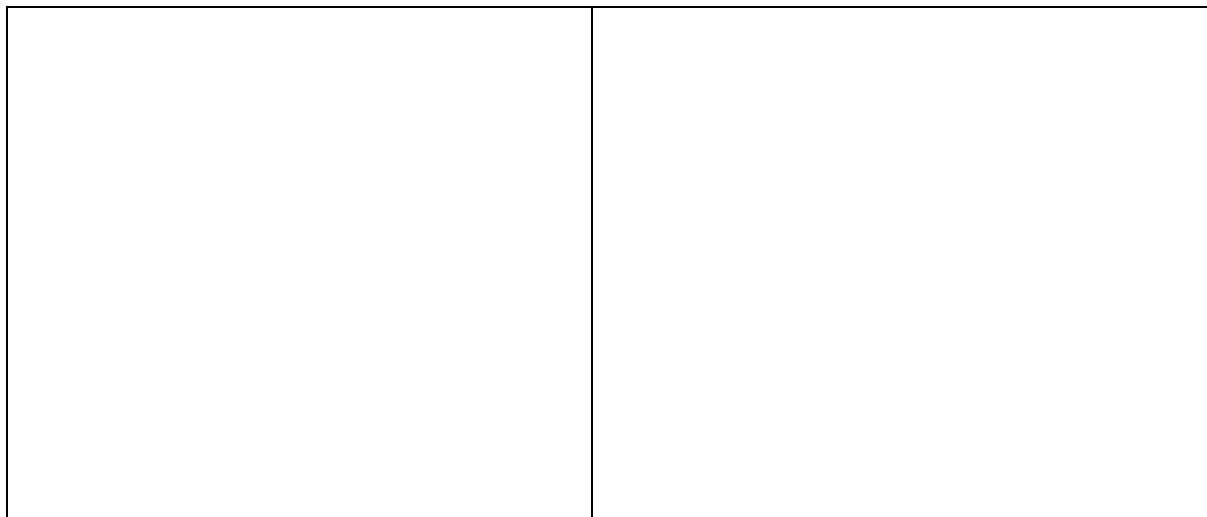


Figure 6. Drain-source on-state resistance



Test circuits and waveforms

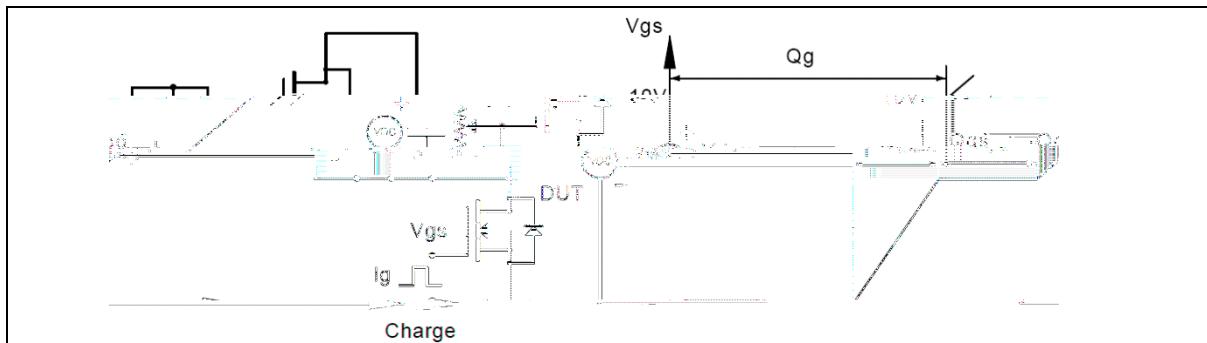


Figure 1. Gate charge test circuit & waveform

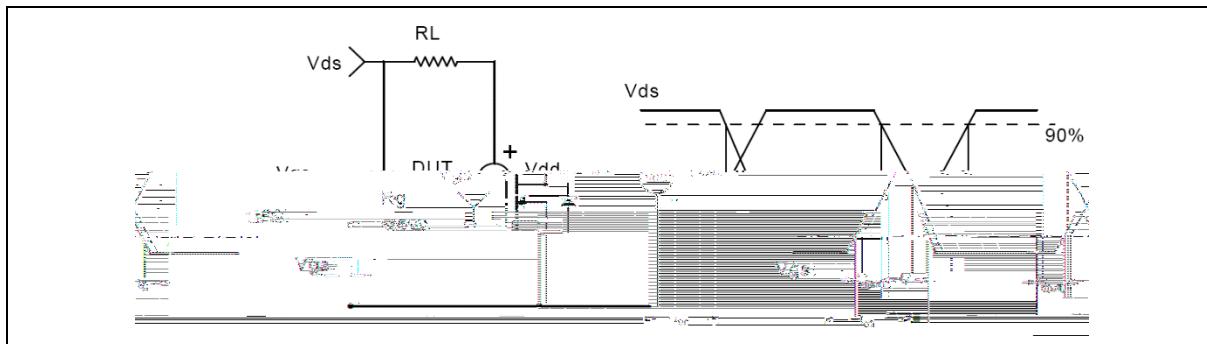


Figure 2. Switching time test circuit & waveform

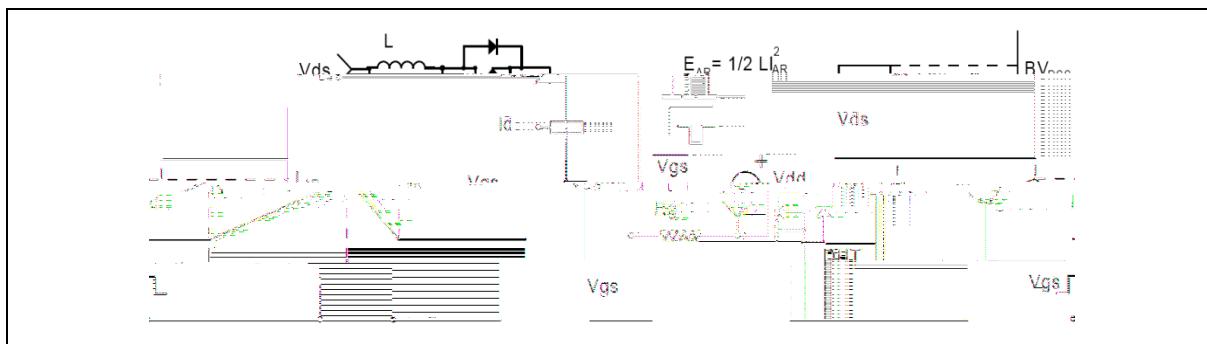


Figure 3. Unclamped inductive switching (UIS) test circuit & waveform

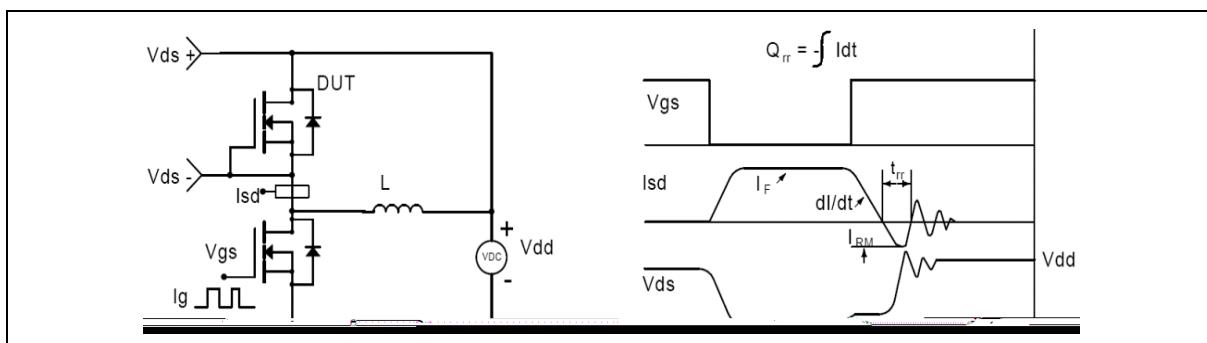


Figure 4. Diode reverse recovery test circuit & waveform

Package Information

Symbol	mm		
	Min	Nom	Max
A	4.40	4.50	4.60
A1	0.00	0.10	0.25
A2	2.20	2.40	2.60

Ordering Information

Package Type	Units/Reel	Reels / Inner Box	Units/Inner Box	Inner Boxes/Carton Box	Units/Carton Box
TO263-J	800	1	800	10	8000

Product Information

Product	Package	Pb Free	RoHS	Halogen Free
SFG100N10KF	TO263	yes	yes	yes

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